

RoHS

HALOGEN

FREE

GREEN



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Vishay Semiconductors

# High Speed Infrared Emitting Diode, 850 nm, Surface Emitter Technology



#### **DESCRIPTION**

TSHG5210 is an infrared, 850 nm emitting diode based on surface emitter chip technology with high radiant power and high speed, molded in a clear, untinted plastic package.

### **FEATURES**

Package type: leadedPackage form: T-1¾

• Dimensions (in mm): Ø 5

• Leads with stand-off

• Peak wavelength: λ<sub>p</sub> = 850 nm

High reliability

• High radiant power

· High radiant intensity

• Angle of half intensity:  $\varphi = \pm 10^{\circ}$ 

Low forward voltage

· Suitable for high pulse current operation

· Good spectral matching with Si photodetectors

 Material categorization: for definitions of compliance please see <a href="https://www.vishav.com/doc?99912"><u>www.vishav.com/doc?99912</u></a>

### **APPLICATIONS**

- Infrared high speed remote control and free air data transmission systems with high modulation frequencies or high data transmission rate requirements
- Transmission systems according to IrDA requirements and for carrier frequency based systems (e.g. ASK/FSK coded, 450 kHz or 1.3 MHz)

PRODUCT SUMMARY					
COMPONENT	I <sub>e</sub> (mW/sr)	φ <b>(°)</b>	$\lambda_{\mathbf{p}}$ (nm)	t <sub>r</sub> (ns)	
TSHG5210	215	± 10	850	10	

#### Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION					
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM		
TSHG5210	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1¾		

### Note

MOQ: minimum order quantity

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>amb</sub> = 25 °C, unless otherwise specified)					
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
Reverse voltage		$V_{R}$	5	V	
Forward current		I <sub>F</sub>	100	mA	
Peak forward current	$t_p/T = 0.5$ , $t_p = 100 \mu s$	I <sub>FM</sub>	200	mA	
Surge forward current	t <sub>p</sub> = 100 μs	I <sub>FSM</sub>	1	Α	
Power dissipation		$P_V$	180	mW	
Junction temperature		Tj	100	°C	
Ambient temperature range		T <sub>amb</sub>	-40 to +85	°C	
Storage temperature range		T <sub>stg</sub>	-40 to +100	°C	
Soldering temperature	t ≤ 5 s, 2 mm from case	T <sub>sd</sub>	260	°C	
Thermal resistance junction to ambient	J-STD-051, leads 7 mm, soldered on PCB	R <sub>thJA</sub>	230	K/W	





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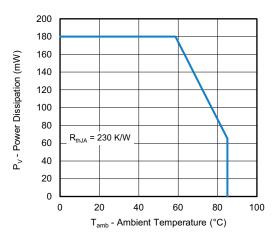


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

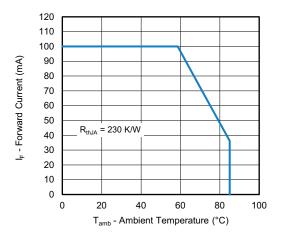


Fig. 2 - Forward Current Limit vs. Ambient Temperature

<b>BASIC CHARACTERISTICS</b> (T <sub>amb</sub> = 25 °C, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	V <sub>F</sub>	=	1.6	1.8	V
	$I_F = 1 \text{ A}, t_p = 100 \mu \text{s}$	V <sub>F</sub>	=	3.0	-	V
Temperature coefficient of V <sub>F</sub>	I <sub>F</sub> = 100 mA	TK <sub>VF</sub>	-	-1.5	-	mV/K
Reverse current		I <sub>R</sub>	Not designed for reverse operation			μA
Junction capacitance	$V_R = 0 \text{ V, } f = 1 \text{ MHz, } E = 0$	Cj	-	53	-	pF
Radiant intensity	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	l <sub>e</sub>	100	215	420	mW/sr
	$I_F = 1 \text{ A}, t_p = 100 \mu \text{s}$	l <sub>e</sub>	=	1595	-	mW/sr
Radiant power	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	фе	-	61	-	mW
Temperature coefficient of φ <sub>e</sub>	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	TΚφ <sub>e</sub>	-	-0.27	-	%/K
Angle of half intensity		φ	=	± 10	-	0
Peak wavelength	I <sub>F</sub> = 100 mA	λρ	-	850	-	nm
Spectral bandwidth	I <sub>F</sub> = 100 mA	Δλ	-	30	-	nm
Temperature coefficient of $\lambda_p$	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	TKλ <sub>p</sub>	-	0.24	-	nm/K
Rise time	I <sub>F</sub> = 100 mA	t <sub>r</sub>	-	10	-	ns
Fall time	I <sub>F</sub> = 100 mA	t <sub>f</sub>	-	10	-	ns

160

150

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I<sub>F</sub> = 100 mA

### BASIC CHARACTERISTICS (T<sub>amb</sub> = 25 °C, unless otherwise specified)

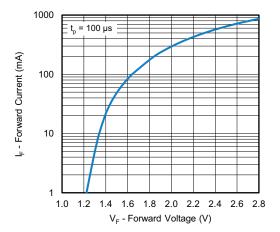
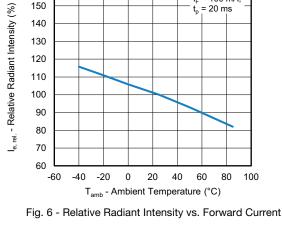


Fig. 3 - Forward Current vs. Forward Voltage



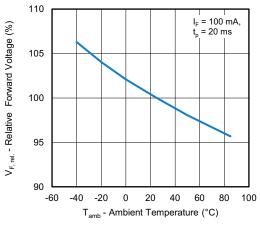


Fig. 4 - Relative Forward Voltage vs. Ambient Temperature

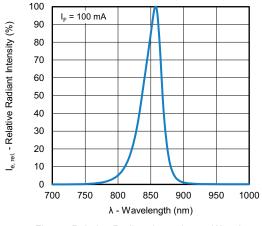


Fig. 7 - Relative Radiant Intensity vs. Wavelength

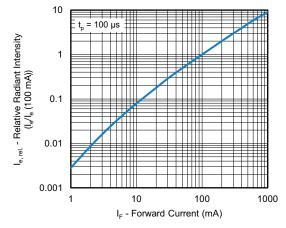


Fig. 5 - Relative Radiant Intensity vs. Forward Current

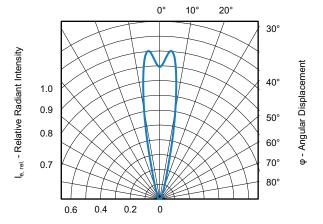


Fig. 8 - Relative Radiant Intensity vs. Angular Displacement

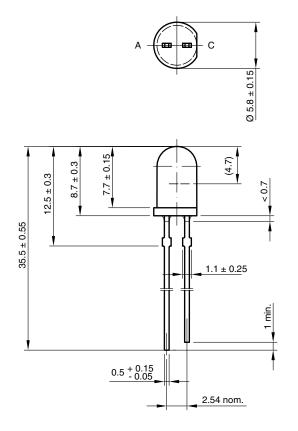
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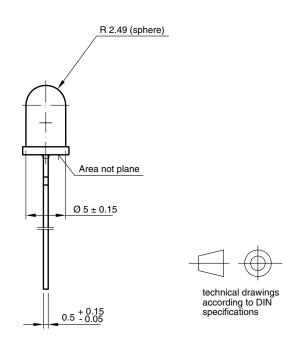


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### **PACKAGE DIMENSIONS** in millimeters





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